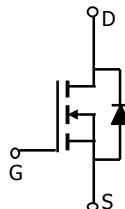


General Description

The AOD476 uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. This device is suitable for use in PWM, load switching and general purpose applications.

Features

V_{DS} (V) = 20V
 I_D = 25A (V_{GS} = 10V)
 $R_{DS(ON)}$ < 21 mΩ (V_{GS} = 10V)
 $R_{DS(ON)}$ < 28 mΩ (V_{GS} = 4.5V)
 $R_{DS(ON)}$ < 79 mΩ (V_{GS} = 2.5V)



Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 16	V
Continuous Drain Current	$T_C=25^\circ\text{C}$ ^G	25	A
Current		20	
Pulsed Drain Current ^C	I_{DM}	75	
Avalanche Current ^C	I_{AR}	13	A
Repetitive avalanche energy $L=0.3\text{mH}$ ^C	E_{AR}	25	mJ
Power Dissipation ^B	$T_C=25^\circ\text{C}$	33.3	W
		16.7	
Power Dissipation ^A	$T_A=25^\circ\text{C}$	2.5	W
		1.6	
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 175	°C

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$t \leq 10\text{s}$	17	25	°C/W
Maximum Junction-to-Ambient ^A		40	50	°C/W
Maximum Junction-to-Case ^B	$R_{\theta JC}$	3.6	4.5	°C/W

Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	$I_D=250\mu\text{A}, V_{GS}=0\text{V}$	20			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=16\text{V}, V_{GS}=0\text{V}$			1	uA
		$T_J=55^\circ\text{C}$			5	
I_{GSS}	Gate-Body leakage current	$V_{DS}=0\text{V}, V_{GS}=\pm 16\text{V}$			100	nA
$V_{\text{GS(th)}}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$	0.6	1.26	2	V
$I_{\text{D(ON)}}$	On state drain current	$V_{GS}=10\text{V}, V_{DS}=5\text{V}$	75			A
$R_{\text{DS(ON)}}$	Static Drain-Source On-Resistance	$V_{GS}=10\text{V}, I_D=20\text{A}$		14	21	mΩ
		$T_J=125^\circ\text{C}$		21		
		$V_{GS}=4.5\text{V}, I_D=10\text{A}$		20	28	
g_{FS}	Forward Transconductance	$V_{GS}=2.5\text{V}, I_D=4\text{A}$		57	79	S
		$V_{DS}=5\text{V}, I_D=20\text{A}$		19		
		$I_S=1\text{A}, V_{GS}=0\text{V}$		0.77	1	V
I_S	Maximum Body-Diode Continuous Current ^G				30	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	$V_{GS}=0\text{V}, V_{DS}=10\text{V}, f=1\text{MHz}$		900		pF
C_{oss}	Output Capacitance			162		pF
C_{rss}	Reverse Transfer Capacitance			105		pF
R_g	Gate resistance	$V_{GS}=0\text{V}, V_{DS}=0\text{V}, f=1\text{MHz}$		0.9	1.35	Ω
SWITCHING PARAMETERS						
$Q_g(10\text{V})$	Total Gate Charge	$V_{GS}=10\text{V}, V_{DS}=10\text{V}, I_D=20\text{A}$		15	18	nC
$Q_g(4.5\text{V})$	Total Gate Charge			7.2	9	nC
Q_{gs}	Gate Source Charge			1.8		nC
Q_{gd}	Gate Drain Charge			2.8		nC
$t_{\text{D(on)}}$	Turn-On Delay Time	$V_{GS}=10\text{V}, V_{DS}=10\text{V}, R_L=0.5\Omega, R_{\text{GEN}}=3\Omega$		4.5		ns
t_r	Turn-On Rise Time			9.2		ns
$t_{\text{D(off)}}$	Turn-Off Delay Time			18.7		ns
t_f	Turn-Off Fall Time			3.3		ns
t_{rr}	Body Diode Reverse Recovery Time	$I_F=20\text{A}, dI/dt=100\text{A}/\mu\text{s}$		18		ns
Q_{rr}	Body Diode Reverse Recovery Charge	$I_F=20\text{A}, dI/dt=100\text{A}/\mu\text{s}$		9.5		nC

A: The value of $R_{\theta JA}$ is measured with the device mounted on 1 in ² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The Power dissipation P_{DSM} is based on $R_{\theta JA}$ and the maximum allowed junction temperature of 150°C . The value in any given application depends on the user's specific board design, and the maximum temperature of 175°C may be used if the PCB allows it.

B. The power dissipation P_D is based on $T_{J(\text{MAX})}=175^\circ\text{C}$, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

C: Repetitive rating, pulse width limited by junction temperature $T_{J(\text{MAX})}=175^\circ\text{C}$.

D. The $R_{\theta JA}$ is the sum of the thermal impedance from junction to case $R_{\theta JC}$ and case to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using <300 μs pulses, duty cycle 0.5% max.

F. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of $T_{J(\text{MAX})}=175^\circ\text{C}$.

G. The maximum current rating is limited by bond-wires.

H. These tests are performed with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The SOA curve provides a single pulse rating.

*This device is guaranteed green after data code 8X11 (Sep 1ST 2008).

Rev2: Oct. 2008

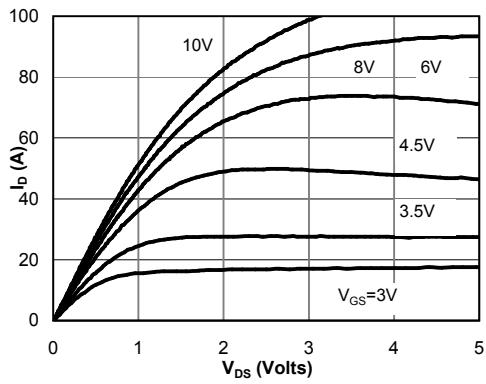
TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS


Fig 1: On-Region Characteristics

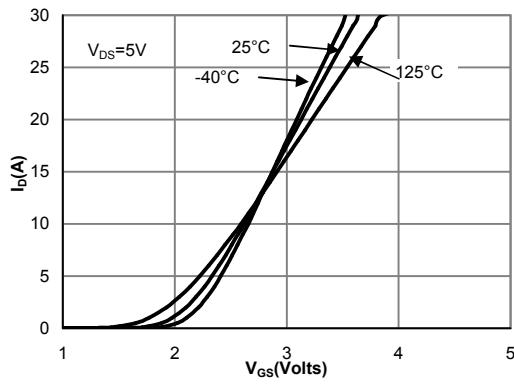


Figure 2: Transfer Characteristics

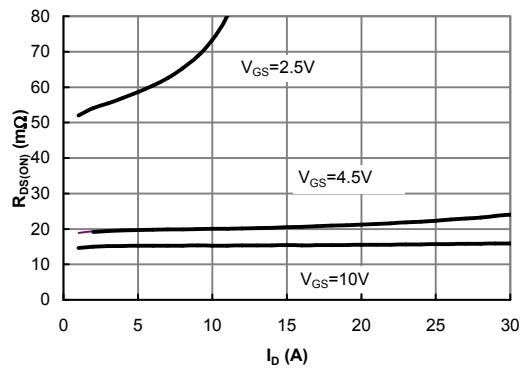


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

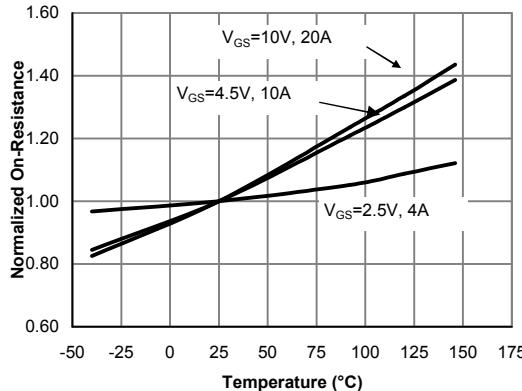


Figure 4: On-Resistance vs. Junction Temperature

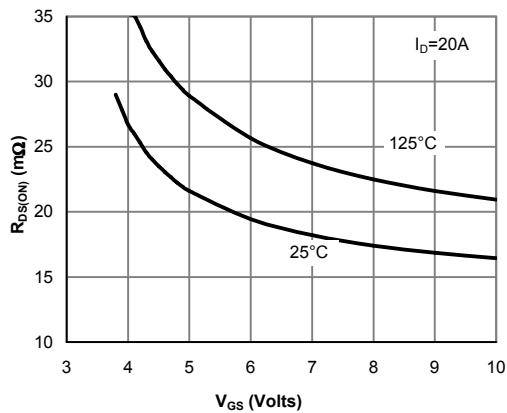


Figure 5: On-Resistance vs. Gate-Source Voltage

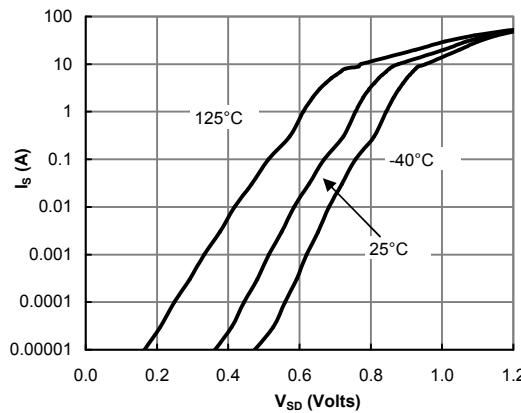


Figure 6: Body-Diode Characteristics

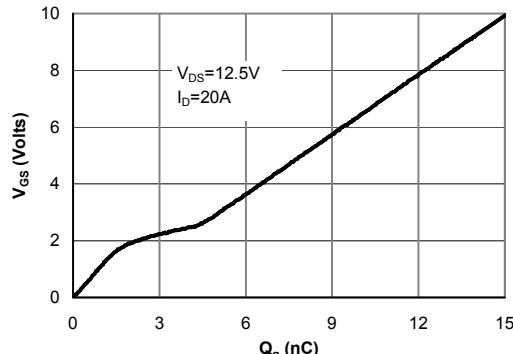
TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS


Figure 7: Gate-Charge Characteristics

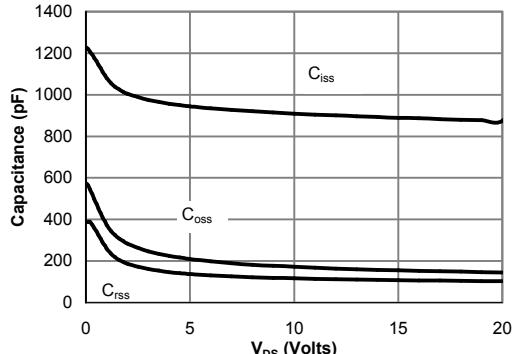


Figure 8: Capacitance Characteristics

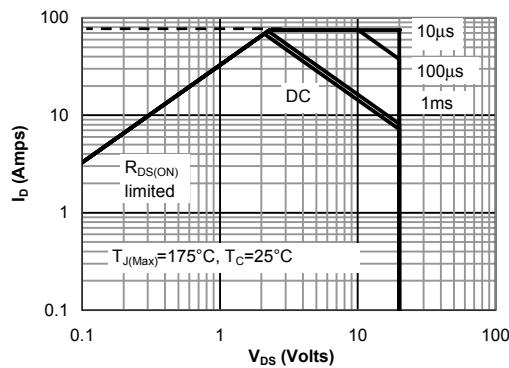


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

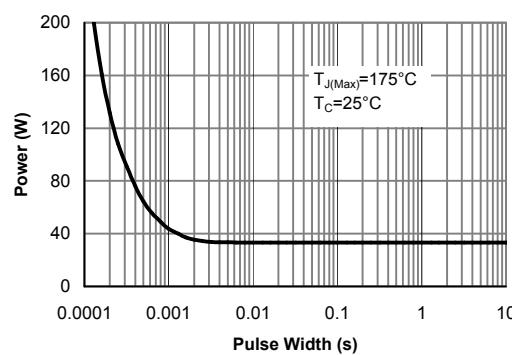


Figure 10: Single Pulse Power Rating Junction-to-Case (Note F)

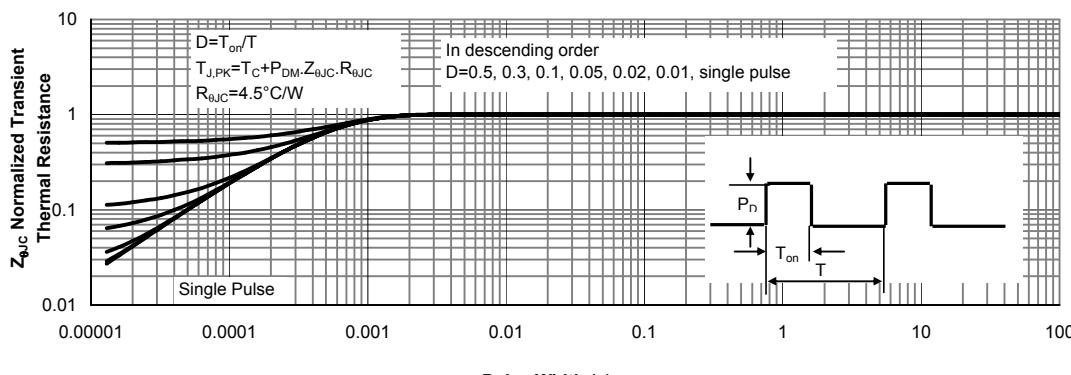
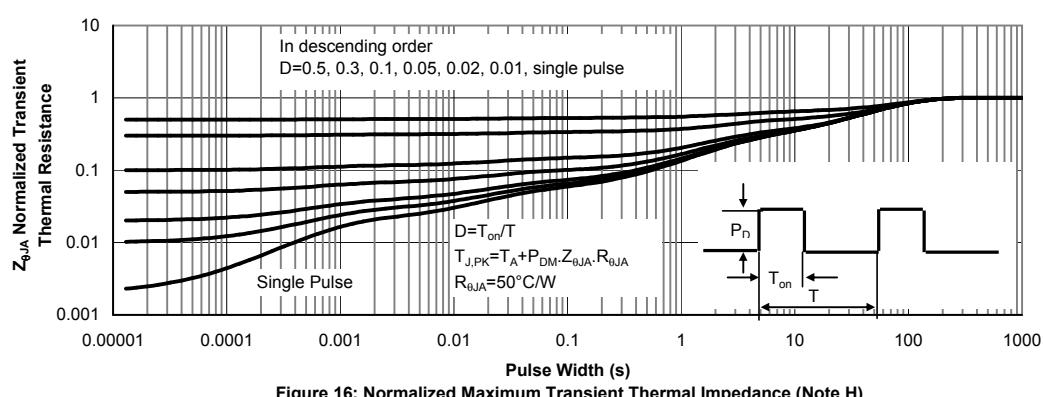
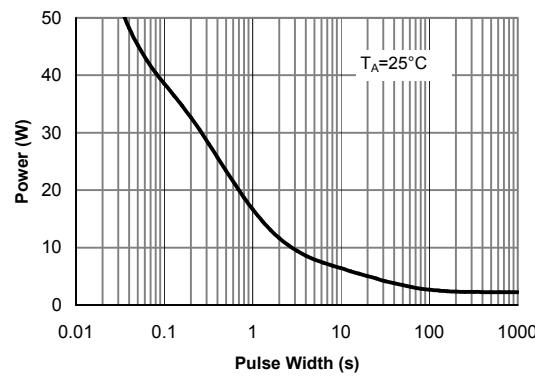
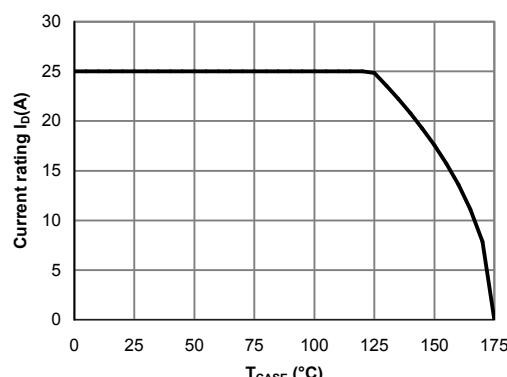
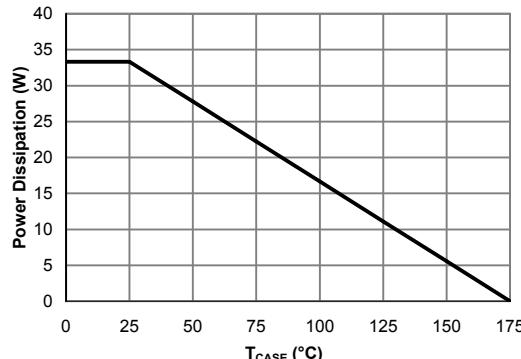
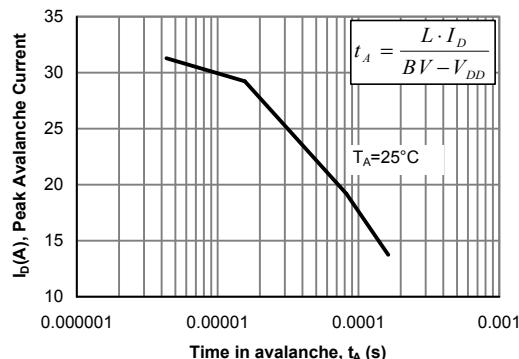
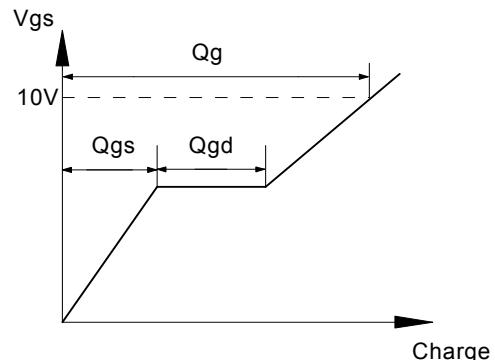
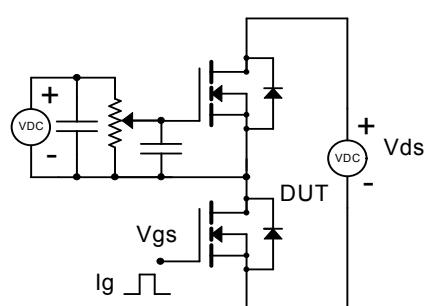


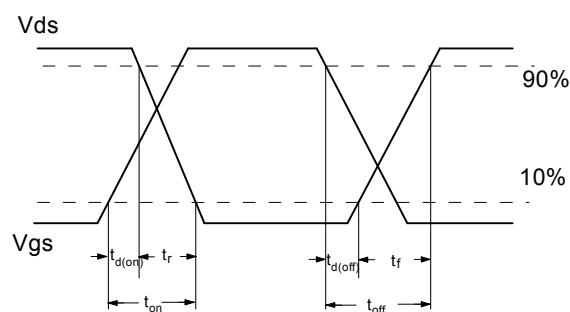
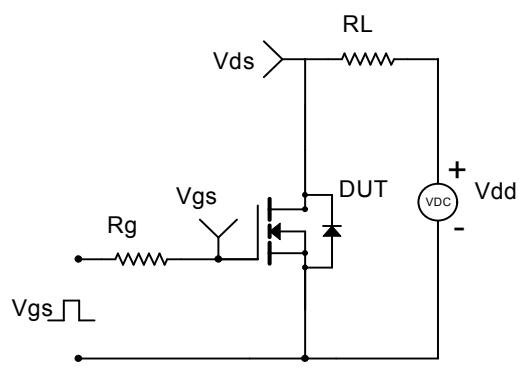
Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS


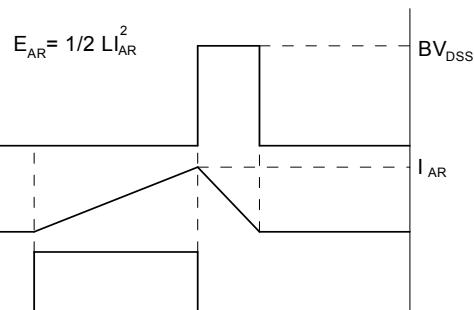
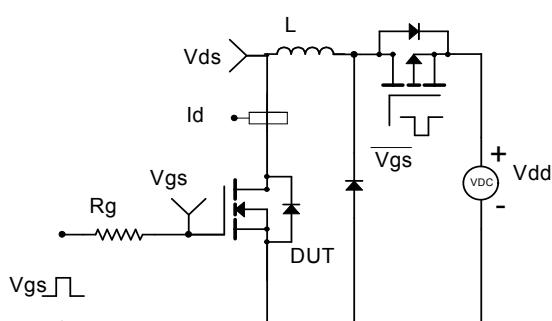
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms

